

ABSTRACT

[0077] A method of fabricating an ultra shallow junction of a field effect transistor is provided. The method includes the steps of etching a substrate near a gate structure to define a source region and a drain region of the transistor, forming a spacer/protective film having poor step coverage to protect frontal surfaces of the source and drain regions, laterally etching sidewalls of the regions beneath a gate dielectric to define a channel region, and removing the protective film.